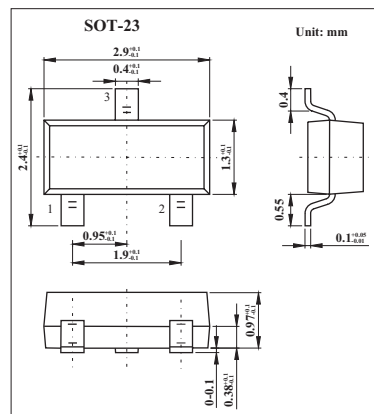


BA779;BA779S

■ Features

- Wide frequency range 10 MHz to 1 GHz



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Test Conditions	Value	Unit
Reverse Voltage	V_R		30	V
Forward Current	I_F		50	mA
Junction Temperature	T_j		125	°C
Storage temperature range	T_{stg}		-55 to +125	°C
Junction ambient	R_{thJA}	on PC board 50mm×50mm×1.6mm	500	K/W

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward Voltage	V_F	$I_F = 20\text{ mA}$			1	V
Reverse Current	I_R	$V_R = 30\text{ V}$			50	nA
Diode capacitance	C_D	$f = 100\text{ MHz}, V_R = 0$			0.5	pF
Differential forward resistance	r_f	$f = 100\text{ MHz}, I_F = 1.5\text{ mA}$			50	Ω
Reverse impedance	BA799 BA799S	$f = 100\text{ MHz}, V_R = 0$	5			K Ω
			9			
Minority carrier lifetime	τ	$I_F = 10\text{ mA}, I_R = 10\text{ mA}$		4		$\mu\text{ S}$